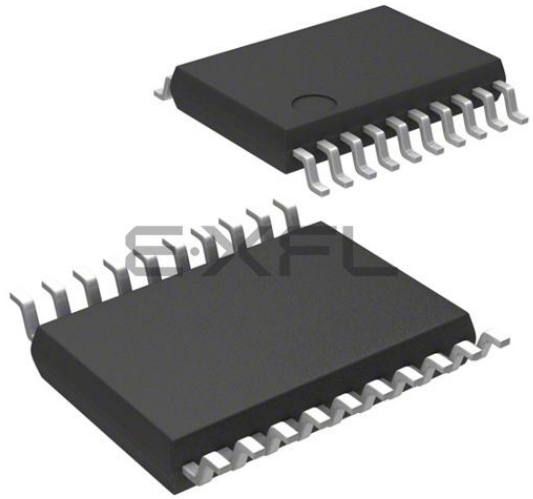

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	640 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s903f3p6

List of figures

2 Description

The STM8S903K3/F3 access line 8-bit microcontrollers offer 8 Kbyte Flash program memory, plus integrated true data EEPROM. The STM8S microcontroller family reference manual (RM0016) refers to devices in this family as low-density. They provide the following benefits: performance, robustness, and reduced system cost.

Device performance and robustness are ensured by advanced core and peripherals made in a state-of-the art technology, a 16 MHz clock frequency, robust I/Os, independent watchdogs with separate clock source, and a clock security system.

The system cost is reduced thanks to an integrated true data EEPROM for up to 300 k write/erase cycles and a high system integration level with internal clock oscillators, watchdog and brown-out reset.

Full documentation is offered as well as a wide choice of development tools.

Table 1. STM8S903K3/F3 access line features

Device	STM8S903K3	STM8S903F3
Pin count	32	20
Maximum number of GPIOs (I/Os)	28(1)	16(2)
Ext. interrupt pins	28	16
Timer CAPCOM channels	7	
Timer complementary outputs	3	2
A/D converter channels	7	5
High sink I/Os	21	12
Low density Flash program memory (bytes)	8K	
Data EEPROM (bytes)	640(3)	
RAM (bytes)	1K	
Peripheral set	Multipurpose timer (TIM1), SPI, I2C, UART window WDG, independent WDG, ADC, PWM timer (TIM5), 8-bit timer (TIM6)	

1. Including 21 high-sink outputs
2. Including 12 high-sink outputs
3. No read-while-write (RWW) capability.

4.2 Single wire interface module (SWIM) and debug module (DM)

The single wire interface module and debug module permits non-intrusive, real-time in-circuit debugging and fast memory programming.

SWIM

Single wire interface module for direct access to the debug module and memory programming. The interface can be activated in all device operation modes. The maximum data transmission speed is 145 bytes/ms.

Debug module

The non-intrusive debugging module features a performance close to a full-featured emulator. Beside memory and peripherals, also CPU operation can be monitored in real-time by means of shadow registers.

- R/W to RAM and peripheral registers in real-time
- R/W access to all resources by stalling the CPU
- Breakpoints on all program-memory instructions (software breakpoints)
- Two advanced breakpoints, 23 predefined configurations

4.3 Interrupt controller

- Nested interrupts with three software priority levels,
- 32 interrupt vectors with hardware priority,
- Up to 28 external interrupts on 7 vectors including TLI,
- Trap and reset interrupts

4.4 Flash program and data EEPROM memory

- 8 Kbyte of Flash program single voltage Flash memory,
- 640 byte true data EEPROM,
- User option byte area.

Write protection (WP)

Write protection of Flash program memory and data EEPROM is provided to avoid unintentional overwriting of memory that could result from a user software malfunction.

There are two levels of write protection. The first level is known as MASS (memory access security system). MASS is always enabled and protects the main Flash program memory, data EEPROM and option bytes.

To perform in-application programming (IAP), this write protection can be removed by writing a MASS key sequence in a control register. This allows the application to write to data EEPROM, modify the contents of main program memory or the device option bytes.

A second level of write protection, can be enabled to further protect a specific area of memory known as UBC (user boot code). Refer to the figure below.

The size of the UBC is programmable through the UBC option byte, in increments of 1 page (64-byte block) by programming the UBC option byte in ICP mode.

Table 5. TSSOP20/SO20/UFQFPN20 pin descriptions (continued)

TSSOP20	UFQFPN20	Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
				floating	wpu	Ext.	High sink(1)	Speed	OD	PP			
19	16	PD2/AIN3/ [TIM5_CH3]	I/O	**X**	X	X	HS	O3	X	X	Port D2	-	Analog input 3 [AFR2] Timer 52 - channel 3 [AFR1]
20	17	PD3/ AIN4/ TIM5_CH2/ ADC_ETR	I/O	**X**	X	X	HS	O3	X	X	Port D3	Analog input 4 Timer 52 - channel 2/ADC external trigger	-
1	18	PD4/ TIM5_CH1/ BEEP [UART1_CK]	I/O	**X**	X	X	HS	O3	X	X	Port D4	Timer 5 - channel 1/BEEP output	UART clock [AFR2]
2	19	PD5/ AIN5/ UART1_TX	I/O	**X**	X	X	HS	O3	X	X	Port D5	Analog input 5/ UART1 data transmit	-
3	20	PD6/ AIN6/ UART1_RX	I/O	**X**	X	X	HS	O3	X	X	Port D6	Analog input 6/ UART1 data receive	-

1. I/O pins used simultaneously for high current source/sink must be uniformly spaced around the package. In addition, the total driven current must respect the absolute maximum ratings (see *Section 10.2: Absolute maximum ratings*).
2. When the MCU is in Halt/Active-halt mode, PA1 is automatically configured in input weak pull-up and cannot be used for waking up the device. In this mode, the output state of PA1 is not driven. It is recommended to use PA1 only in input mode if Halt/Active-halt is used in the application.
3. In the open-drain output column, ‘T’ defines a true open-drain I/O (P-buffer, weak pull-up, and protection diode to VDD are not implemented)
4. The PD1 pin is in input pull-up during the reset phase and after internal reset release.

5.6 Alternate function remapping

As shown in the rightmost column of the pin description table, some alternate functions can be remapped at different I/O ports by programming one of eight AFR (alternate function remap) option bits. When the remapping option is active, the default alternate function is no longer available.

To use an alternate function, the corresponding peripheral must be enabled in the peripheral registers.

Alternate function remapping does not effect GPIO capabilities of the I/O ports (see the GPIO section of the family reference manual, RM0016).

6.2.2 General hardware register map

Table 8. General hardware register map

Address	Block	Register label	Register name	Reset status
0x00 501E to 0x00 5059	Reserved area (60 byte)			
0x00 505A	Flash	FLASH_CR1	Flash control register 1	0x00
0x00 505B		FLASH_CR2	Flash control register 2	0x00
0x00 505C		FLASH_NCR2	Flash complementary control register 2	0xFF
0x00 505D		FLASH _FPR	Flash protection register	0x00
0x00 505E		FLASH _NFPR	Flash complementary protection register	0xFF
0x00 505F		FLASH _IAPSR	Flash in-application programming status register	0x00
0x00 5060 to 0x00 5061	Reserved area (2 byte)			
0x00 5062	Flash	FLASH _PUKR	Flash program memory unprotection register	0x00
0x00 5063	Reserved area (1 byte)			
0x00 5064	Flash	FLASH _DUKR	Data EEPROM unprotection register	0x00
0x00 5065 to 0x00 509F	Reserved area (59 byte)			
0x00 50A0	ITC	EXTI_CR1	External interrupt control register 1	0x00
0x00 50A1		EXTI_CR2	External interrupt control register 2	0x00
0x00 50A2 to 0x00 50B2	Reserved area (17 byte)			
0x00 50B3	RST	RST_SR	Reset status register	0xXX(1)
0x00 50B4 to 0x00 50BF	Reserved area (12 byte)			
0x00 50C0	CLK	CLK_ICKR	Internal clock control register	0x01
0x00 50C1		CLK_ECKR	External clock control register	0x00
0x00 50C2	Reserved area (1 byte)			

Table 8. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5400	ADC1 cont'd	ADC_CSR	ADC control/status register	0x00
0x00 5401		ADC_CR1	ADC configuration register 1	0x00
0x00 5402		ADC_CR2	ADC configuration register 2	0x00
0x00 5403		ADC_CR3	ADC configuration register 3	0x00
0x00 5404		ADC_DRH	ADC data register high	0xXX
0x00 5405		ADC_DRL	ADC data register low	0xXX
0x00 5406		ADC_TDRH	ADC Schmitt trigger disable register high	0x00
0x00 5407		ADC_TDRL	ADC Schmitt trigger disable register low	0x00
0x00 5408		ADC_HTRH	ADC high threshold register high	0x03
0x00 5409		ADC_HTRL	ADC high threshold register low	0xFF
0x00 540A		ADC_LTRH	ADC low threshold register high	0x00
0x00 540B		ADC_LTRL	ADC low threshold register low	0x00
0x00 540C		ADC_AWSRH	ADC analog watchdog status register high	0x00
0x00 540D		ADC_AWSRL	ADC analog watchdog status register low	0x00
0x00 540E		ADC _AWCRH	ADC analog watchdog control register high	0x00
0x00 540F		ADC_AWCRL	ADC analog watchdog control register low	0x00
0x00 5410 to 0x00 57FF	Reserved area (1008 byte)			

1. Depends on the previous reset source.
2. Write-only register.

Table 10. Interrupt mapping (continued)

IRQ no.	Source block	Description	Wakeup from halt mode	Wakeup from active-halt mode	Vector address
20	Reserved	-	-	-	0x00 8058
21	Reserved	-	-	-	0x00 805C
22	ADC1	ADC1 end of conversion/ analog watchdog interrupt	-	-	0x00 8060
23	TIM6	TIM6 update/ overflow	-	-	0x00 8064
24	Flash	EOP/WR_PG_DIS	-	-	0x00 8068
Reserved					0x00 806C to 0x00 807C

1. Except PA1.

2. Refer to STM8S903K3 pin descriptions.

Table 14. STM8S903F3 alternate function remapping bits [7:2] for 20-pin packages

Option byte no.	Description(1)
OPT2	**AFR7** Alternate function remapping option 7 0: AFR7 remapping option inactive: Default alternate functions.(2) 1: Port C3 alternate function = TIM1_CH1N; port C4 alternate function = TIM1_CH2N. **AFR6** Alternate function remapping option 6 Reserved. **AFR5** Alternate function remapping option 5 Reserved. **AFR4** Alternate function remapping option 4 0: AFR4 remapping option inactive: Default alternate functions.(2) 1: Port B4 alternate function = ADC_ETR; port B5 alternate function = TIM1_BKIN. **AFR3** Alternate function remapping option 3 0: AFR3 remapping option inactive: Default alternate function.(2) 1: Port C3 alternate function = TLI. **AFR2** Alternate function remapping option 2 Reserved.

1. Do not use more than one remapping option in the same port.
2. Refer to STM8S903K3 pin descriptions.

Table 15. STM8S903K3 alternate function remapping bits [1:0] for 32-pin packages

AFR1 option bit value	AFR0 option bit value	I/O port	Alternate function mapping
0	0	AFR1 and AFR0 remapping options inactive: Default alternate functions(1)	
0	1	PC5	TIM5_CH1
		PC6	TIM1_CH1
		PC7	TIM1_CH2
1	0	PA3	SPI_NSS
		PD2	TIM5_CH3

Table 23. Total current consumption with code execution in run mode at V_{DD} = 5 V (continued)

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
$I_{DD(RUN)}$	Supply current in Run mode, code executed from Flash	$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	4.5	-	mA
			HSE user ext. clock (16 MHz)	4.3	4.75	
			HSI RC osc. (16 MHz)	3.7	4.5	
		$f_{CPU} = f_{MASTER}$ = 2 MHz	HSI RC osc. (16 MHz/8)(2)	0.84	1.05	
		$f_{CPU} = f_{MASTER}$ /128 = 125 kHz	HSI RC osc. (16 MHz)	0.72	0.9	
		$f_{CPU} = f_{MASTER}$ /128 = 15.625 kHz	HSI RC osc. (16 MHz/8)	0.46	0.58	
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.42	0.57	

1. Guaranteed by characterization results. Guaranteed by characterization results.
2. Default clock configuration measured with all peripherals off.

Table 24. Total current consumption with code execution in run mode at V_{DD} = 3.3 V

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
$I_{DD(RUN)}$	Supply current in Run mode, code executed from RAM	$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	1.8	-	mA
			HSE user ext. clock (16 MHz)	2	2.35	
			HSI RC osc. (16 MHz)	1.5	2	
		$f_{CPU} = f_{MASTER}$ /128 = 125 kHz	HSE user ext. clock (16 MHz)	0.81	-	
			HSI RC osc. (16 MHz)	0.7	0.87	
		$f_{CPU} = f_{MASTER}$ /128 = 15.625 kHz	HSI RC osc. (16 MHz/8)	0.46	0.58	
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.41	0.55	
$I_{DD(RUN)}$	Supply current in Run mode, code executed from Flash	$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	4	-	mA
			HSE user ext. clock (16 MHz)	3.9	4.7	
			HSI RC osc. (16 MHz)	3.7	4.5	
		$f_{CPU} = f_{MASTER}$ = 2 MHz	HSI RC osc. (16 MHz/8)(2)	0.84	1.05	
		$f_{CPU} = f_{MASTER}$ /128 = 125 kHz	HSI RC osc. (16 MHz)	0.72	0.9	
		$f_{CPU} = f_{MASTER}$ /128 = 15.625 kHz	HSI RC osc. (16 MHz/8)	0.46	0.58	
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.42	0.57	

1. Guaranteed by characterization results.
2. Default clock configuration measured with all peripherals off.

2. Measured from interrupt event to interrupt vector fetch
3. $t_{WU(WFI)} = 2 \times 1/f_{master} + 67 \times 1/f_{CPU}$
4. Configured by the REGAH bit in the CLK_ICKR register.
5. Configured by the AHALT bit in the FLASH_CR1 register.
6. Plus 1 LSI clock depending on synchronization.

Total current consumption and timing in forced reset state

Table 32. Total current consumption and timing in forced reset state

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$I_{DD(R)}$	Supply current in reset state(2)	V_{DD} = 5 V	400	-	µA
		V_{DD} = 3.3 V	300	-	
$t_{RESETBL}$	Reset pin release to vector fetch	-	-	150	µs

1. Guaranteed by design.
2. Characterized with all I/Os tied to V_{SS}.

Current consumption of on-chip peripherals

Subject to general operating conditions for V_{DD} and T_A.

HSI internal RC/f_{CPU}= f_{MASTER} = 16 MHz, V_{DD} = 5 V

Table 33. Peripheral current consumption

Symbol	Parameter	Typ	Unit
$I_{DD(TIM1)}$	TIM1 supply current(1)	210	µA
$I_{DD(TIM5)}$	TIM5 supply current(1)	130	
$I_{DD(TIM6)}$	TIM6 supply current(1)	50	
$I_{DD(UART1)}$	UART1 supply current (2)	120	
$I_{DD(SPI)}$	SPI supply current (2)	45	
$I_{DD(I2C)}$	I2C supply current(2)	65	
$I_{DD(ADC1)}$	ADC1 supply current when converting(3)	1000	

1. Data based on a differential I_{DD} measurement between reset configuration and timer counter running at 16 MHz. No IC/OC programmed (no I/O pads toggling). Not tested in production.
2. Data based on a differential IDD measurement between the on-chip peripheral when kept under reset and not clocked and the on-chip peripheral when clocked and not kept under reset. No I/O pads toggling. Not tested in production.
3. Data based on a differential IDD measurement between reset configuration and continuous A/D conversions. Not tested in production.

Current consumption curves

The following figures show typical current consumption measured with code executing in RAM.

HSE crystal/ceramic resonator oscillator

The HSE clock can be supplied with a 1 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 35. HSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE}	External high speed oscillator frequency	-	1	-	16	MHz
R_F	Feedback resistor	-	-	220	-	kΩ
$C^{(1)}$	Recommended load capacitance(2)	-	-	-	20	pF
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF f_{OSC} = 16 MHz	-	-	6 (start up) 1.6 (stabilized)(3)	mA
		C = 10 pF f_{OSC} = 16 MHz	-	-	6 (start up) 1.2 (stabilized)(3)	
g_m	Oscillator transconductance	-	5	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	1	-	ms

1. C is approximately equivalent to 2 x crystal Cload.
2. The oscillator selection can be optimized in terms of supply current using a high quality resonator with small Rm value. Refer to crystal manufacturer for more details
3. Guaranteed by characterization results.
4. $t_{SU(HSE)}$ is the start-up time measured from the moment it is enabled (by software) to a stabilized 16 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Figure 22. Typical V_{IL} and V_{IH} vs V_{DD} @ 4 temperatures

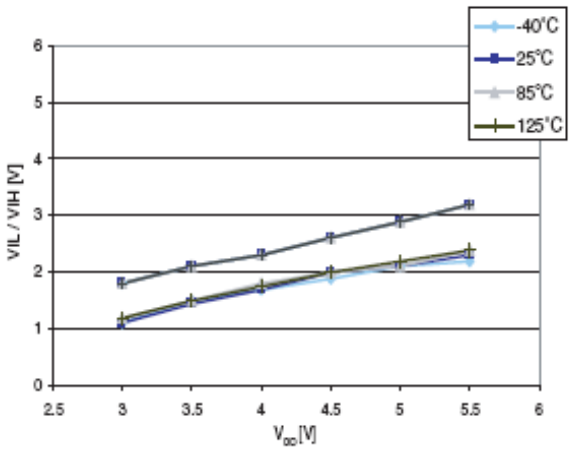


Figure 23. Typical pull-up current vs V_{DD} @ 4 temperatures

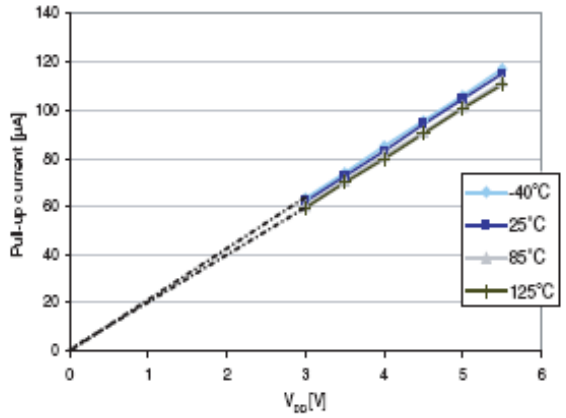


Figure 24. Typical pull-up resistance vs VDD @ 4 temperatures

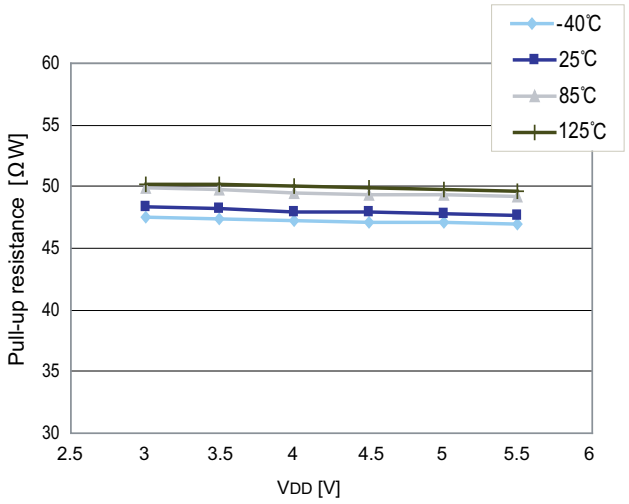


Table 41. Output driving current (standard ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO}= 10 mA, V_{DD} = 5 V	-	2.0	V
	Output low level with 4 pins sunk	I_{IO}= 4 mA, V_{DD} = 3.3 V	-	1.0(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO}= 10 mA, V_{DD} = 5 V	2.8	-	
	Output high level with 4 pins sourced	I_{IO}= 4 mA, V_{DD} = 3.3 V	2.1(1)	-	

1. Guaranteed by characterization results

Table 42. Output driving current (true open drain ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 2 pins sunk	I_{IO}= 10 mA, V_{DD} = 5 V	-	1.0	V
	Output low level with 2 pins sunk	I_{IO}= 10 mA, V_{DD} = 3.3 V	-	1.5(1)	
V_{OH}	Output high level with 2 pins sourced	I_{IO}= 10 mA, V_{DD} = 5 V	-	2.0(1)	

1. Guaranteed by characterization results

Table 43. Output driving current (high sink ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO}= 10 mA, V_{DD} = 5 V	-	0.8	V
	Output low level with 4 pins sunk	I_{IO}= 10 mA, V_{DD} = 3.3 V	-	1.0(1)	
		I_{IO}= 20 mA, V_{DD} = 5 V	-	1.5(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO}= 10 mA, V_{DD} = 5 V	4.0	-	
	Output high level with 4 pins sourced	I_{IO}= 10 mA, V_{DD} = 3.3 V	2.1(1)	-	
		I_{IO}= 20 mA, V_{DD} = 5 V	3.3(1)	-	

1. Guaranteed by characterization results.

Figure 25. Typ. V_{OL} @ V_{DD} = 3.3 V (standard ports)

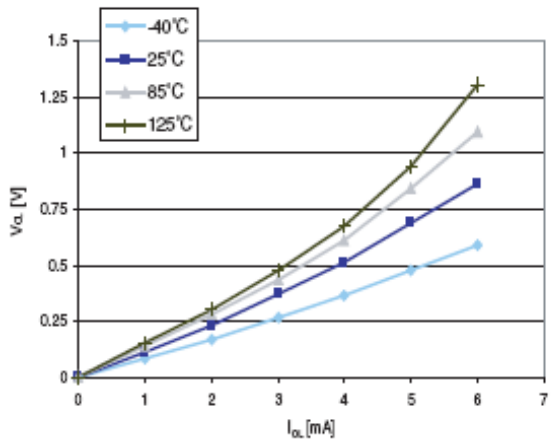


Figure 26. Typ. V_{OL} @ V_{DD} = 5.0 V (standard ports)

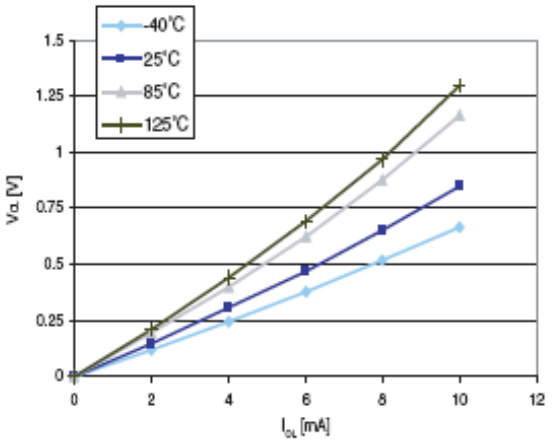


Figure 27. Typ. V_{OL} @ V_{DD} = 3.3 V (true open drain ports)

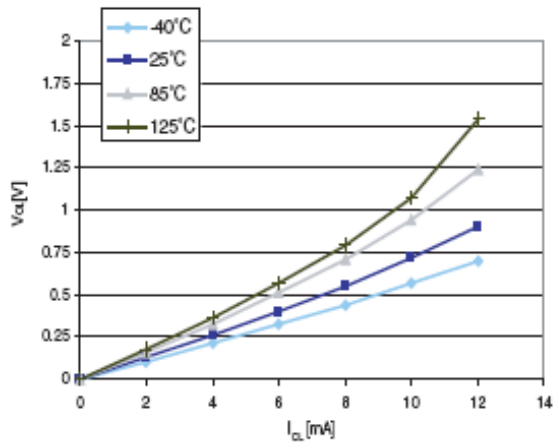


Figure 28. Typ. V_{OL} @ V_{DD} = 5.0 V (true open drain ports)

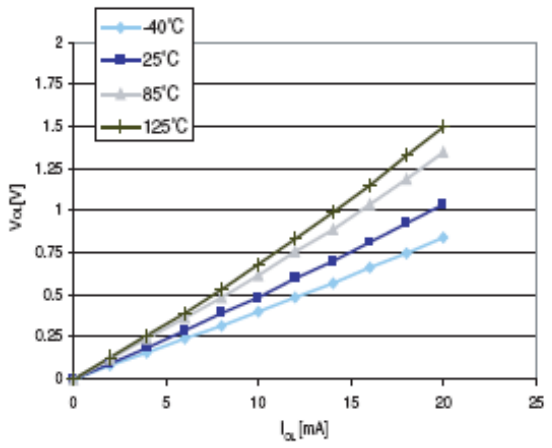


Figure 29. Typ. V_{OL} @ V_{DD} = 3.3 V (high sink ports)

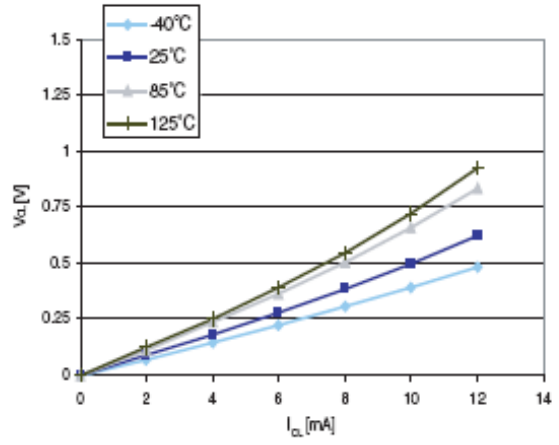
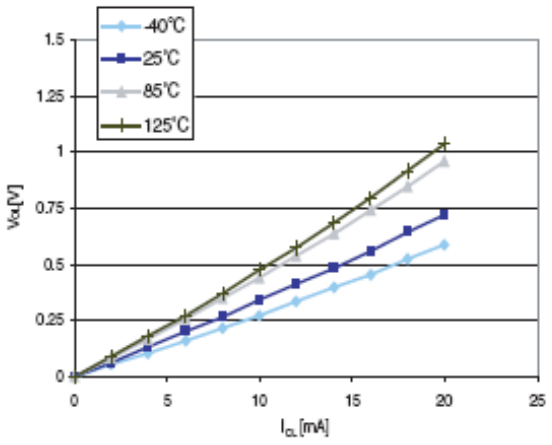


Figure 30. Typ. V_{OL} @ V_{DD} = 5.0 V (high sink ports)



10.3.10 10-bit ADC characteristics

Subject to general operating conditions for V_{DDA}, f_{MASTER}, and T_A unless otherwise specified.

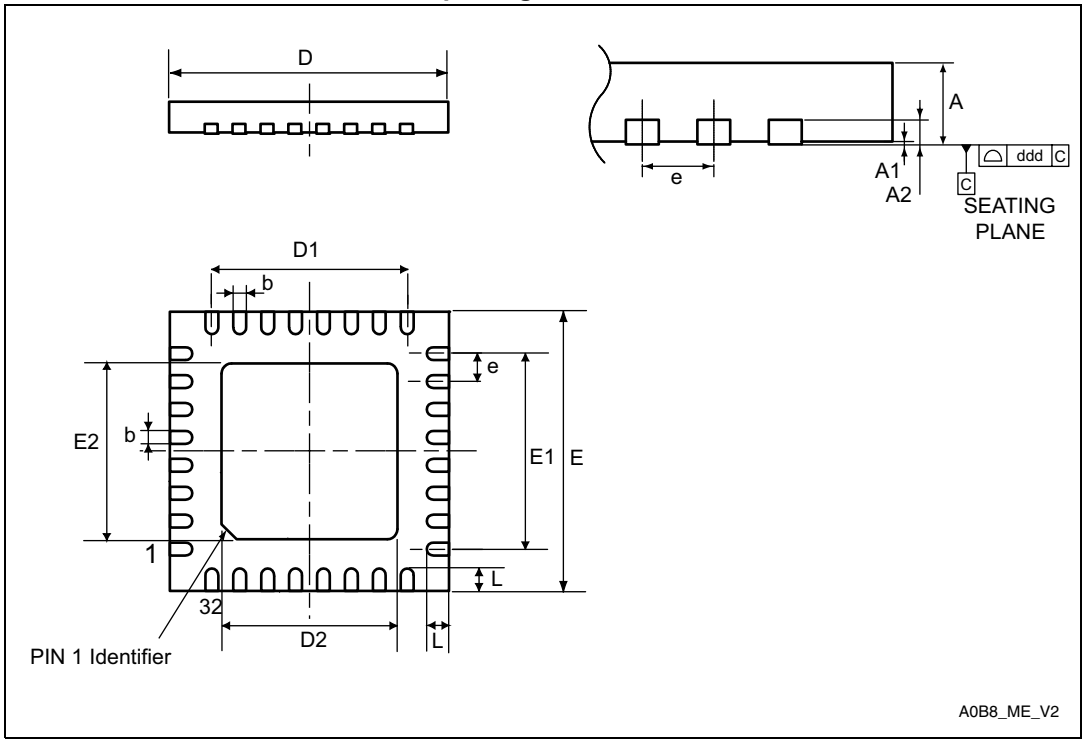
Table 47. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	V_{DD}= 2.95 to 5.5 V	1	-	4	MHz
		V_{DD}= 4.5 to 5.5 V	1	-	6	
V_{AIN}	Conversion voltage range(1)	-	V_{SS}	-	V_{DD}	V
V_{BGREF}	Internal bandgap reference voltage	V_{DD} = 2.95 to 5.5 V	1.19	1.22	1.25	V
C_{ADC}	Internal sample and hold capacitor	-	-	3	-	pF
t_S(1)	Minimum sampling time	f_{ADC} = 4 MHz	-	0.75	-	µs
		f_{ADC} = 6 MHz	-	0.5	-	
t_{STAB}	Wakeup time from standby	-	-	7.0	-	µs
t_{CONV}	Minimum total conversion time (including sampling time, 10-bit resolution)	f_{ADC} = 4 MHz	3.5			µs
		f_{ADC} = 6 MHz	2.33			µs
		-	14			$1/f_{ADC}$

1. During the sample time, the sampling capacitance, C_{AIN} (3 pF max), can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sample time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

11.2 UFQFPN32 package information

Figure 48. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package outline



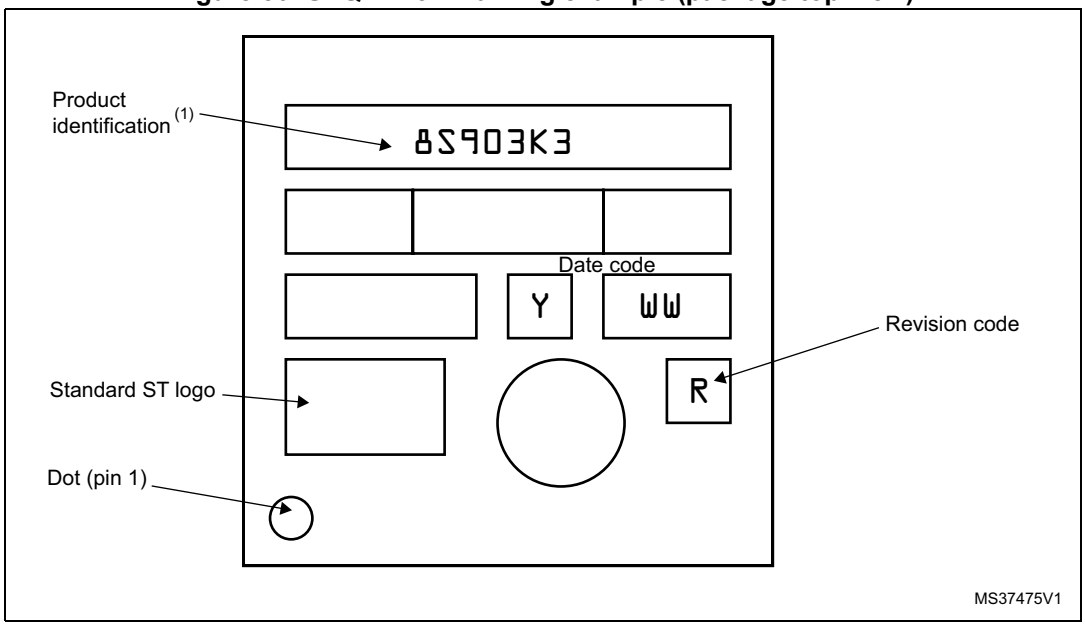
1. Drawing is not to scale.
2. All leads/pads should be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this backside pad to PCB ground.
4. Dimensions are in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 50. UFQFPN32 marking example (package top view)



1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

12 Thermal characteristics

The maximum junction temperature (T_{Jmax}) of the device must never exceed the values specified in *Table 21: General operating conditions*, otherwise the functionality of the device cannot be guaranteed.

The maximum junction temperature T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in ° C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 60. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient TSSOP20 - 4.4mm	110	°C/W
	Thermal resistance junction-ambient SO20W (300 mils)	20	
	Thermal resistance junction-ambient UFQFPN20 - 3 x 3 mm	101	
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm	60	
	Thermal resistance junction-ambient UFQFPN32 - 5 x 5 mm	38	
	Thermal resistance junction-ambient SDIP32 - 400 mils	60	

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

12.1 Reference document

JESD51-2 integrated circuits thermal test method environment conditions - natural convection (still air). Available from www.jedec.org.

Table 61. Document revision history (continued)

Date	Revision	Changes
08-Sep-2010	5	Removed VFQFPN32 package. Updated the definition for reset state in *Table 4: Legend/abbreviations for pinout tables* Updated pins 13/25/20, 14/26/21, 19/32/27, 1/2/29, 2/3/30, and 3/4/31; added footnote to PD1/SWIM pin in *Table 6: STM8S903K3 UFQFPN32/LQFP32/SDIP32 pin descriptions*. Standardized all reset state values; updated the reset state values of RST_SR, CLK_SWCR, CLK_HSITRIMR, CLK_SWIMCCR, IWDG_KR, and ADC_DRx registers in *Table 8: General hardware register map*. Changed the caption of *Table 13: STM8S903K3 alternate function remapping bits [7:2] for 32-pin packages*. Added *Table 14: STM8S903F3 alternate function remapping bits [7:2] for 20-pin packages*. Changed the caption of *Table 15: STM8S903K3 alternate function remapping bits [1:0] for 32-pin packages*. Added *Table 16: STM8S903F3 alternate function remapping bits [1:0] for 20-pin packages*. Replaced 0.01 µF with 0.1 µF in *Figure 38: Recommended reset pin protection*. Added *Figure 42: Typical application with I^2C bus and timing diagram*. Updated footnote 1 in *Table 48: ADC accuracy with R_{AIN}< 10 kΩ, V_{DD}= 5 V* and *Table 49: ADC accuracy with R_{AIN}< 10 kΩ, V_{DD}= 3.3 V*. Updated existing footnote and added three additional footnotes to *Table 55: UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data*. Updated the special marking and OPT2 alternate function remapping sections in *Section 13.1: STM8S903K3/F3 FASTROM microcontroller option list*.